



LEO ICs specification overview

Introduction

Rad-hard ICs in a plastic package are an optimized solution for LEO constellation mission profiles. Taking full advantage of its over 40-year Space heritage and its automotive AEC-Q100 qualified production lines, STMicroelectronics is introducing a new series of rad-hard components in plastic packages to support the growing Low Earth Orbit satellites market. Compliant with ST's LEO generic specification for ICs, these space-ready and automotive-based products offer a specific trade-off among footprint size savings, cost of ownership and quality assurance together with radiation hardness and large quantity capacity.

Benefits:

- Low cost of ownership
- · Radiation proven in TID and SEE
- AEC-Q100 based
- Dedicated qualification level
- · Screening and traceability
- Large quantity capacity
- Lightweight
- Whisker-free finishing (NiPdAu)
- Single plant source per line



LEO ICs flow and supply chain

LEO ICs' flow and supply chain are compliant with "ST LEO generic specification", with ST SOP267 (Finished Good Maturity Management) and with ST procedure 8161393 (General Specification for Product development).

Front-End **Product** Order & supply **Final Test** Radiation **Diffusion** Qualification in Rennes On AEC-Q100 qualified lines On AEC-Q100 qualified lines PAT/GPAT as As per MIL-STD-883 Space-certified plant per AEC-Q100

Figure 1. LEO IC's flow

Key benefits:

- ST proprietary flow from design to delivery
- Optimised flow for small to medium quantities
- Only radiation and taping are subcontracted, managed by ST Rennes space-certified plant
- Product qualification performed by ST Rennes space-certified plant

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2 LEO ICs product versions

Table 1. Product versions

Version	Specification	Order code	
		Examples:	
Dummy samples	- Worst case final packaging for mounting qualification	- TSSOP20-DUM1	
	- Over-marking : DUM	- PSO20-DUM1	
		- PSO36-DUM1	
	- Final die and final package		
	- Guaranteed at 25°C only	Examples:	
Davidan mant as mulas	- Not provided with any radiation hardness guarantee	- LEOAD128PT-D	
Development samples	- Not submitted to any package testing (thermal cycles, etc.)	- LEOLVDSRDPT-D	
(see TN1418 on st.com)	- Not guaranteed for reliability	- LEO3910PDT-D	
	- Delivered without Certificate of Conformance (CoC)	(see datasheets)	
	- Marking with prefix "D" (ex: DLEOAD128)		
	- Qualified as per "ST LEO Generic Specification"	Examples:	
	- Delivered with Certificate of Conformance (CoC)	- LEOAD128PT	
Flight Models (FM)	- Max. date code : 5 year	- LEOLVDSRDPT	
	- Marking : Part number (ex: LEOAD128)	- LEO3910PDT	
	- Packing : Tape & Reel	(see datasheets on st.com)	

Figure 2. Examples of dummy samples



Figure 3. Examples of development samples



Figure 4. Examples of flight models





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3 Quality assurance level overview

Table 2. Quality assurance level overview

Range			Commercial	Automotive	LEO	Rad-hard	
Specification				AEC-Q100	« ST LEO »	QMLV / ESCC	
Plants	Frond-end	100% IDM (Integrated Device Manufacturer),		V	√		
rialits	Back-end	AEC-Q100 qualified lines		,	Y		
Assembly		Outgassing			√		
		Die shear test (die glue, leadframe adhesion,)	V	V	√	V	
	Process control	Wire pull test	√	√	√	√	
	on each lot	Ball shear test	√	√	√	√	
		X-ray		√	√	√	
		CSAM (for delamination)		√	√		
	QA gate	Optical inspection after sawing (die integrity), before molding (die placement, wire loop height), package integrity (PAO, lead burrs, corrosion)	V	V	V	V	
	Temp. cycling	On all delivered units at -65/+150°C		√	√	√	
Test	Production test	Tested at 3 temperatures		optional	-40/+25/+125	-55/+25/+125	
		EWS	optional	PAT/GPAT	PAT/GPAT	√	
	TID	At wafer lot acceptance test			50	50/100/300	
De dietien	TNID	At wafer lot acceptance test			3.10 ¹¹		
Radiation	SEL	On qualification lot			Up to 62	Up to 125	
	SET/SEU/SEFI	On qualification lot			optional	√	
QA	Serialization / data log by unit					V	
	Single assy T&F plant	Guaranteed by product line		V	V	√	
Cto	Data storage	10 years			√	√	
Storage	Packaged units	5 years			√	√	

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4 Simplified LEO ICs qualification flow

Table 3. LEO ICs' qualification flow

Item	Description	Reference	
Decign and validation	Samples assembled in TSSOP20/PSO20/PSO36	ST documentation: DMS 8161393, SOP26	
Design and validation	Characterization on bench	31 documentation. Divis 6161393, 30F267	
	Outgassing (RML < 1%, CVCM < 0.1%)	As per ASTM E 595	
	HTOL	JESD22-A108	
	HTSL	JESD22-A103	
	EWS		
	UHAST		
	ТНВ		
	Temperature cycling		
Engineering and qualification	Solderability	ST documentation: DMS 8161393, SOP267	
	LU		
	ESD HBM		
	ESD CDM		
	128h life test (max. Vcc, max. Temp. 125°C)		
	SEE		
	TID	MIL-STD-883 TM 1019	
	TNID	MIL-STD-883 TM 1017	
	Final test	ST documentation: DMS 8161393, SOP267	
Production	2000h operating life test (max. Vcc, max. Temp. 125°C)		
	Datasheet published on st.com		

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Simplified LEO ICs manufacturing & control

Table 4. Simplified LEO ICs' manufacturing & control

Item		Description	Reference	
	Die attach	Glue or solder preform	As per AEC-Q100	
Package materials and control	Molding Epoxy resin		As per AEC-Q100	
	Bonding	Gold wires	As per AEC-Q100	
	Lead-finish	Solderability and wettability test (NiPdAu lead-frame)	As per ASTM E 595	
	Outgassing	RML < 1%, CVCM < 0.1%	As per ASTM E 595	
	Die shear test	As per AEC-Q100	MIL-STD-883 Method 2019	
	Wire pull test	As per AEC-Q100	MIL-STD-883 Method 2011	
	Ball shear test	As per AEC-Q100	AEC-Q100 / AEC-Q003	
	X-Ray	Visual check	ST documentation: DM0087783	
	CSAM	(for delamination)	J-SDT-020D	
		50 krad (Si) on each new lot.		
	TID (Total Ionizing Dose)	High dose rate for pure CMOS ICs, High+Low dose rate for BICMOS ICs.	MIL-STD-883 TM 1019	
Dadieties	TNID (Total Non-Ionizing Dose)	3.10 ¹¹ protons / cm ²	MIL-STD-883 TM 1017	
Radiation	SEL @ 125°C	43 MeV.cm²/mg minimum guaranteed,		
	SET/SEU	tested up to 62 MeV.cm²/mg.	ST LEO generic specification	
	SEFI	On product range accordingly (ADC/DAC etc)		
Vafer lot acceptance	WLAT (Wafer Lot Acceptance Test)	EWS + TID + 1000h Life-test.	ST LEO generic specification	
QA	Wafer fab	Yes	SOP243 (traceability procedure)	
	Reel filling	Max. 2 lots per reel, as per ST rules		
	Single assy test & finishing plant	Yes (per line)		
Storage	Data storage	10-year		
	Packaged	5-year		
PCN/PTN	Change and termination process	Space-like	ST LEO generic specification	

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6 Available documentation for LEO ICs

- Datasheet (on st.com)
- CoC (on delivery of products)
- Summary qualification report (on-demand)
- ST LEO generic specification (on-demand)
- PCN/PTN (in case of change and termination of products)

6.1 Certificate of conformance (CoC) content

- Customer name
- ST order confirmation number
- ST part number
- Marking information
- Shipped quantity
- Date code
- Wafer lot identification number
- Diffusion plant
- Wafer lot acceptance test (WLAT) reference
- Radiation verification test (RVT) reference
- Product datasheet reference
- Reference of the "ST LEO generic specification"
- Assy site & test site identification

6.2 Summary qualification report content

- General information
 - Radiation (*)
 - SEE
- Test results
 - Lot information
- Test group A
 - Accelerated environment stress tests
- Test group B
 - Accelerated lifetime simulation tests
- Test group E
 - Electrical verification
 - Treacebility
 - Wafer fab
 - Assembly
 - Accelerated lifetime simulation tests
 - Accelerated environment stress tests

(*) Performance is guaranteed at post TID (see datasheet).

Drifts in TID are not provided, however the data can be shown through audit.

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7 Glossary

Table 5. Acronyms list

Acronyms	Description	
AEC	Automotive Electronics Council	
Au Ni Pd	Gold Nickel Palladium	
BE	Back-end	
CDM	Electrostatic Discharge – Charged Device Model	
CoC	Certificate of Conformity	
CSAM	Confocal Scanning Acoustic Microscopy	
CVCM	Collected volatile condensable material	
ESD	Electrostatic discharge	
GPAT	Geographical Part Average Testing	
HAST	Biased HAST (Highly Accelerated Stress Test)	
НВМ	Electrostatic Discharge - Human Body Model	
HTOL	High Temperature Operating Life	
HTSL	High Temperature Storage Life	
FE	Front-end	
IC	Integrated circuit	
LU	Latch-up	
MSL	Moisture Sensitivity Level	
PAT	Part Average Testing	
PC	Preconditioning	
RML	Recovered mass loss	
SAM	Scanning Acoustic Microscopy	
SEL	Single event latch-up	
SET	Single event transient	
SEU/SEFI	Single event upset / functional interrupt	
TC	Thermal Cycle	
ТНВ	Temperature Humidity Bias	
TSSOP	Thin shrink small outline package	
UHAST	Unbiased HAST (Highly Accelerated Stress Test)	
WBP	Wire Bond Pull	
WBS	Wire Bond Shear	
WLAT	Wafer lot acceptance test	
XRAY	X-ray inspection	

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Revision history

Table 6. Document revision history

Date	Version	Changes
31-Jan-2023	1	Initial release.
11-Oct-2023	2	Updated TNID radiation description in Table 4.
11-Jul-2024	3	Updated Package materials and control in Table 4.

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